

**Y76KPR**  
PHASE CONTROL THYRISTOR

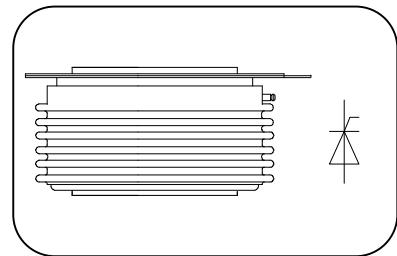
**Features:**

- Center amplifying gate
- Metal case with ceramic insulator
- Low on-state and switching losses

**Typical Applications**

- AC controllers
- DC and AC motor control
- Controlled rectifiers

**I<sub>T(AV)</sub>**      **2434 A**  
**V<sub>DRM/V<sub>RRM</sub></sub>**    **5600-6500V**  
**I<sub>TSM</sub>**        **29.2 KA**  
**I<sup>2</sup>t**           **4263 10<sup>3</sup>A<sup>2</sup>S**



SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T <sub>J</sub> (°C)	VALUE			UNIT
				Min	Type	Max	
I <sub>T(AV)</sub>	Mean on-state current	180° half sine wave 50Hz Double side cooled, T <sub>hs</sub> =55°C	125			2434	A
V <sub>DRM</sub> V <sub>RRM</sub>	Repetitive peak off-state voltage Repetitive peak reverse voltage	V <sub>DRM</sub> &V <sub>RRM</sub> tp=10ms V <sub>DSM</sub> &V <sub>RSM</sub> = V <sub>DRM</sub> &V <sub>RRM</sub> +100V	125	5600		6500	V
I <sub>DRM</sub> I <sub>RRM</sub>	Repetitive peak current	V <sub>DM</sub> = V <sub>DRM</sub> V <sub>RM</sub> = V <sub>RRM</sub>	125			250	mA
I <sub>TSM</sub>	Surge on-state current	10ms half sine wave	125			29.2	KA
I <sup>2</sup> t	I <sup>2</sup> T for fusing coordination	V <sub>R</sub> =0.6V <sub>RRM</sub>				4263	A2s*103
V <sub>TO</sub>	Threshold voltage		125			1.20	V
r <sub>T</sub>	On-state slop resistance					0.28	m□
V <sub>TM</sub>	Peak on-state voltage	I <sub>TM</sub> =1600A, F=40KN	125			1.65	V
dv/dt	Critical rate of rise of off-state voltage	V <sub>DM</sub> =0.67V <sub>DRM</sub>	125			800	V/μs
di/dt	Critical rate of rise of on-state current	V <sub>DM</sub> = 67%V <sub>DRM</sub> to 4000A, Gate pulse tr ≤0.5μs IGM=1.5A Repetitive	125			200	A/μs
I <sub>rrm</sub>	Reverse recovery current		125			250	A
t <sub>rr</sub>	Reverse recovery time	IT <sub>M</sub> =2000A, tp=1000μs, di/dt=-20A/μs, V <sub>r</sub> =50V				26	μs
Q <sub>rr</sub>	Recovery charge					3250	μC
I <sub>GT</sub>	Gate trigger current		25	40		300	mA
V <sub>GT</sub>	Gate trigger voltage	VA=12V, IA=1A		0.8		3.0	V
I <sub>H</sub>	Holding current			20		250	mA
V <sub>GD</sub>	Non-trigger gate voltage	V <sub>DM</sub> =67%V <sub>DRM</sub>	125	0.3			V
R <sub>th(j-h)</sub>	Thermal resistance Junction to heat sink	At 180° sine double side cooled Clamping force 40.0KN				0.010	°C /W
F <sub>m</sub>	Mounting force			35		47	KN
T <sub>stg</sub>	Stored temperature			-40		140	°C
W <sub>t</sub>	Weight				1100		g
Outline		KT73dT					

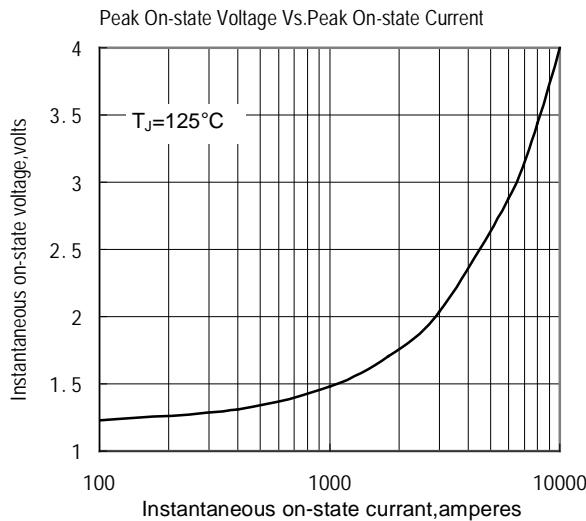


Fig.1

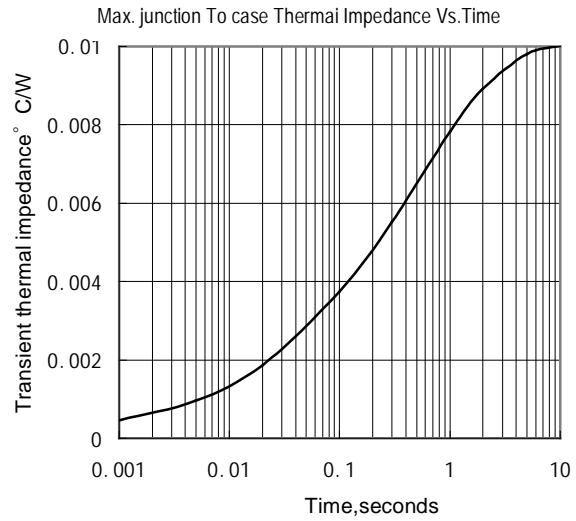


Fig.2

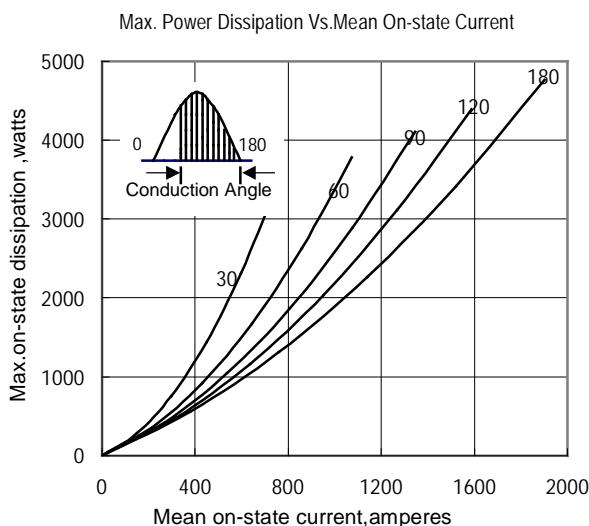


Fig.3

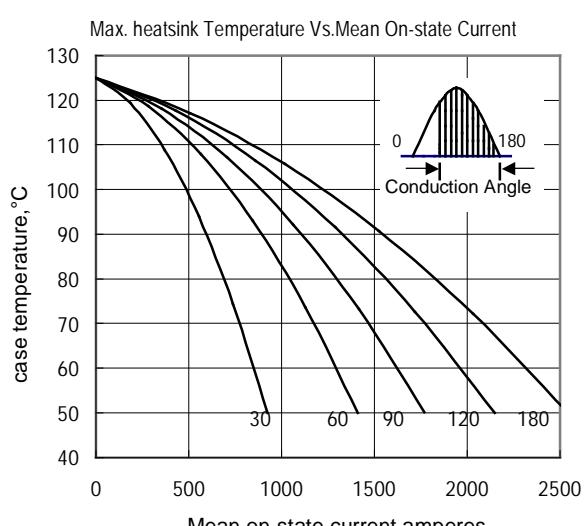


Fig.4

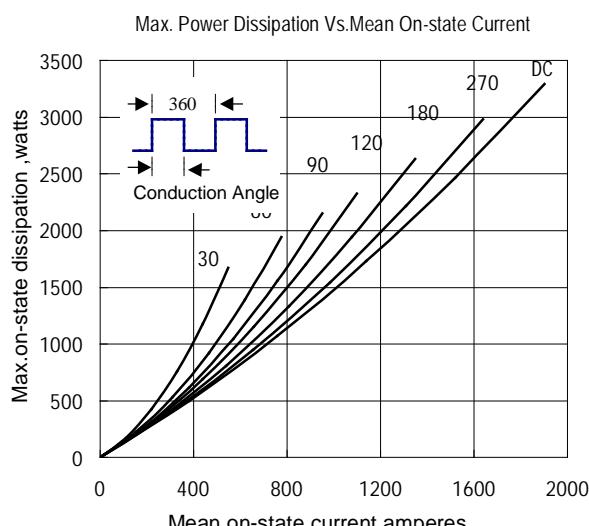


Fig.5

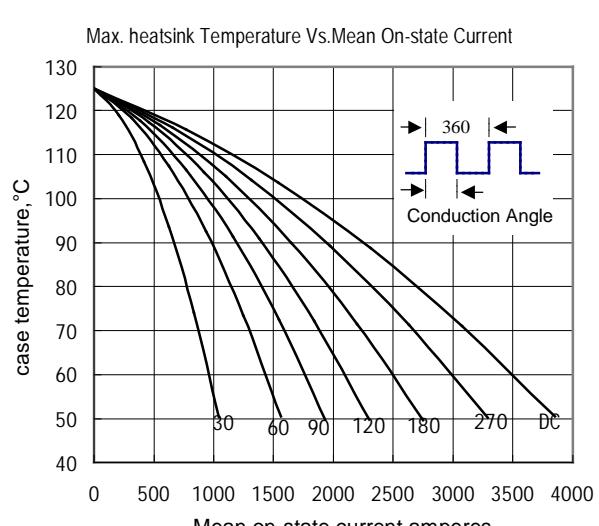


Fig.6

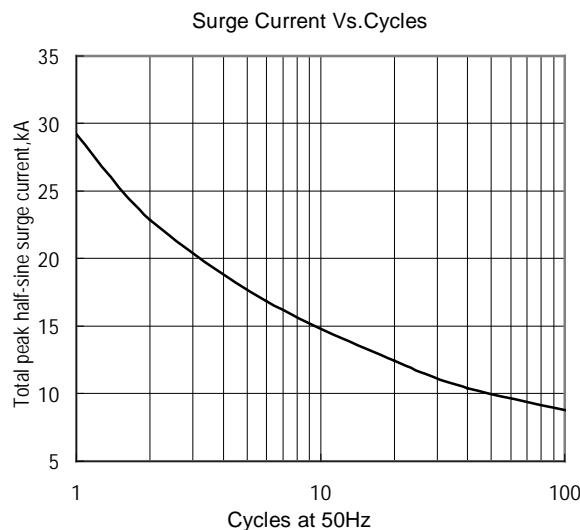


Fig.7

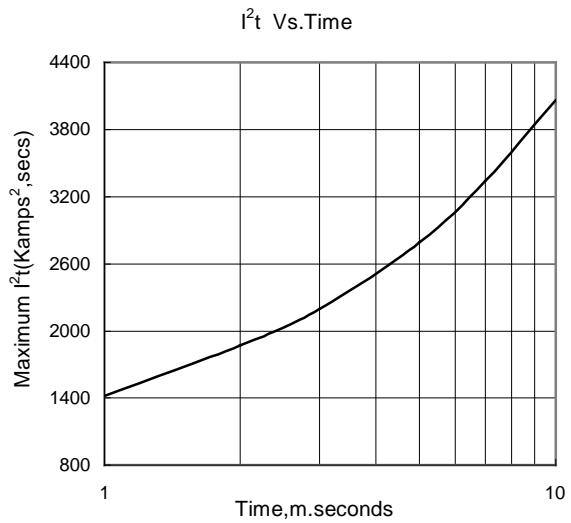


Fig.8

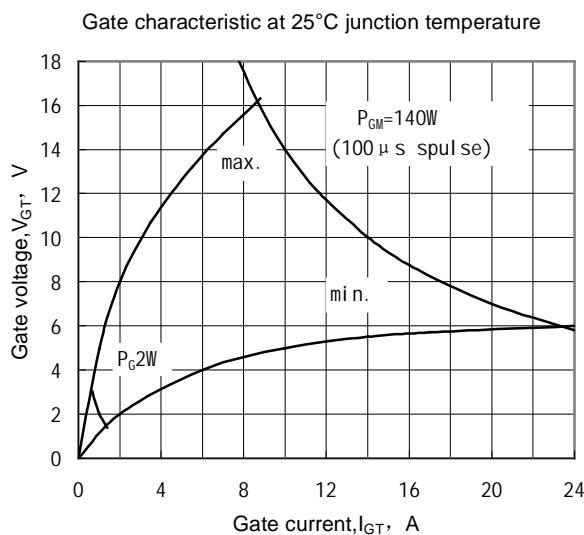


Fig.9

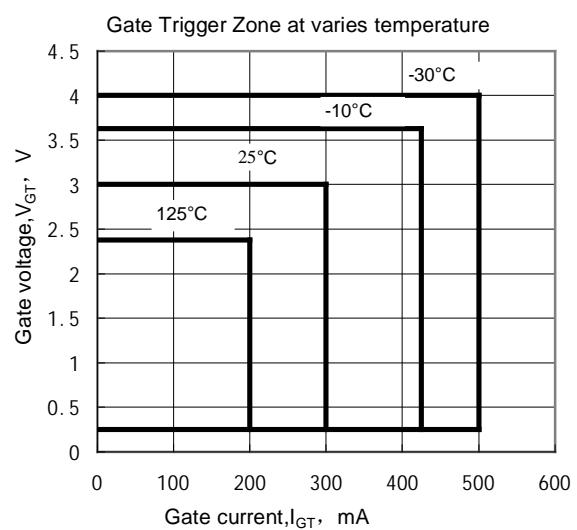


Fig.10

### Outline:

